

Vishay Siliconix

Dual N-Channel 75 V (D-S) 175 °C MOSFET

DESCRIPTION

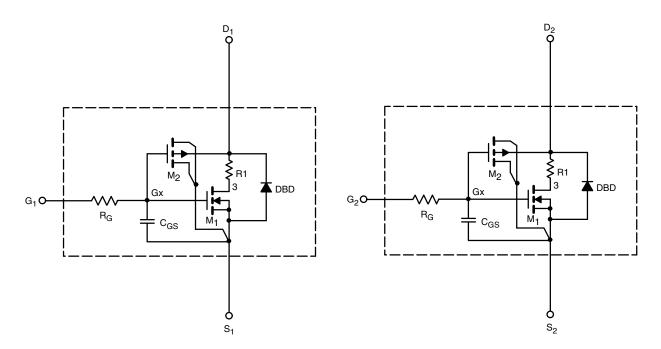
The attached SPICE model describes the typical electrical characteristics of the n-channel vertical DMOS. The sub-circuit model is extracted and optimized over the -55 $^{\circ}\text{C}$ to +125 $^{\circ}\text{C}$ temperature ranges under the pulsed 0 V to 10 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched $C_{\rm gd}$ model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- N-Channel Vertical DMOS
- Macro Model (Sub-circuit Model)
- Level 3 MOS
- · Apply for both Linear and Switching Application
- Accurate over the -55 °C to +125 °C Temperature Range
- Model the Gate Charge

SUBCIRCUIT MODEL SCHEMATIC



Note

• This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits.



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SPECIFICATIONS (T _J = 25 °C, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}$, $I_D = 250 \mu A$	2	2	٧
Drain-Source On-State Resistance ^a	R _{DS(on)}	$V_{GS} = 10 \text{ V}, I_D = 3.8 \text{ A}$	0.041	0.041	Ω
		$V_{GS} = 4.5 \text{ V}, I_D = 3.3 \text{ A}$	0.053	0.055	
Forward Transconductance ^a	9 _{fs}	$V_{DS} = 15 \text{ V}, I_D = 3.8 \text{ A}$	12	14	S
Diode Forward Voltage	V _{SD}	I _S = 2.4 A	0.8	0.8	V
Dynamic ^b					
Input Capacitance	C _{iss}	$V_{DS} = 35 \text{ V}, V_{GS} = 0 \text{ V}, f = 1 \text{ MHz}$	659	630	pF
Output Capacitance	C _{oss}		86	84	
Reverse Transfer Capacitance	C _{rss}		37	36	
Total Gate Charge	Qg		11	14	
Gate-Source Charge	Q _{gs}	V_{DS} = 35 V, V_{GS} = 10 V, I_D = 9.7 A	2.3	2.3	nC
Gate-Drain Charge	Q_{gd}		2.9	2.9	

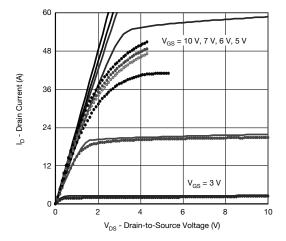
Notes

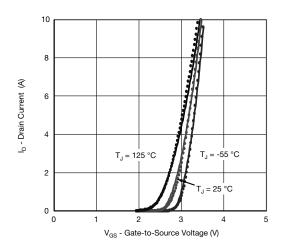
- a. Pulse test; pulse width \leq 300 μ s, duty cycle \leq 2 %.
- b. Guaranteed by design, not subject to production testing.

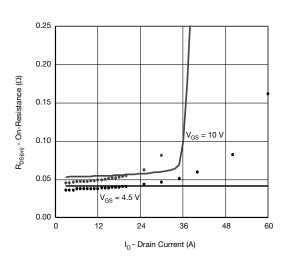
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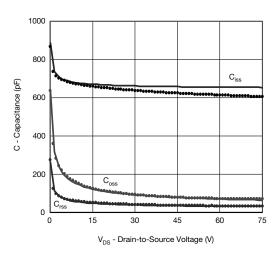
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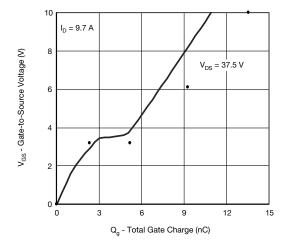
COMPARISON OF MODEL WITH MEASURED DATA ($T_J = 25~^{\circ}\text{C}$, unless otherwise noted)

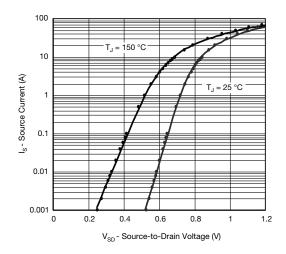












Note

Dots and squares represent measured data.
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